

ELECTRICALLY ISOLATED PILLARS IN SILICON ACTIVE DEVICES

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ABSTRACT

A method of forming an active device is provided. The method includes performing a first patterning operation on a first plurality of layers. This first patterning operation defines a first feature of the active device. Then, a second patterning operation can be performed on at least one layer of the first plurality of layers. This second patterning operation defines a second feature of the active device. Of importance, the first and second patterning operations are performed substantially back-to-back, thereby ensuring that the active device can accurately function.